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| FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT | ATTY. DOCKET 033035 M 0342 | SERIAL NO. 10/691,569 |
| | APPLICANT: Kensaku MOTOKI, et al. | |
| | FILING DATE October 24, 2003 | GROUP ART UNIT 2814 |

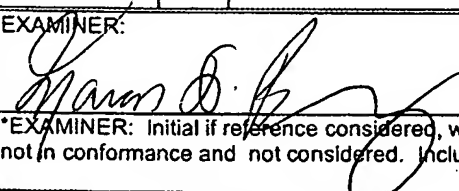
U.S. PATENT DOCUMENTS

| *Examiner's Initials | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB- CLASS | FILING DATE, IF APPROPRIATE |
|-------------------------|----|--------------------|------|------|-------|---------------|--------------------------------|
| | AA | | | | | | |
| | AB | | | | | | |
| | AC | | | | | | |
| | AD | | | | | | |
| | AF | | | | | | |
| | AG | | | | | | |
| | AH | | | | | | |
| | AI | | | | | | |
| | AJ | | | | | | |
| | AK | | | | | | |

FOREIGN PATENT DOCUMENTS

| *Examiner's Initials | | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUB- CLASS | TRANSLATION YES NO | |
|-------------------------|----|--------------------|------|---------|-------|---------------|-----------------------|--|
| | AL | | | | | | | |
| | AM | | | | | | | |
| | AN | | | | | | | |
| | AO | | | | | | | |
| | AP | | | | | | | |

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

| | | |
|---|----|---|
| LA | AQ | Nam et al. "Growth of GaN and Al _{0.8} Ga _{0.2} N on Patterened Substrates via Organometallic Vapor Phase Epitaxy" Jpn.j. Appl. Phys. Vol 36 (May 1, 1997), Pt. 2, No. 5A, pg. L532 |
| | AR | |
| | AS | |
| EXAMINER:  | | DATE CONSIDERED: 2/19/2007 |
| *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | |